

SYSTEM AND METHOD FOR MEASURING PROPERTIES OF A SEMICONDUCTOR SUBSTRATE IN A NON-DESTRUCTIVE WAY

Abstract of the Disclosure

One aspect of the invention discloses a method of determining the dopant profile of doped regions in a semiconductor substrate. A pump laser is used to create excess carriers in this semiconductor substrate. The excess carrier concentration will influence the reflection of a probe laser. From the reflected probe laser not only the bulk components but also the near-surface components are eliminated to only yield the bulk components.

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